

**1. Material**            Substrate      GaAs    (N Type)  
                                  Epitaxial Layer GaAs    (P/N Type)

**2. Electrode**            N(Cathode) Side Gold Alloy  
                                  P(Anode) Side Aluminum Alloy

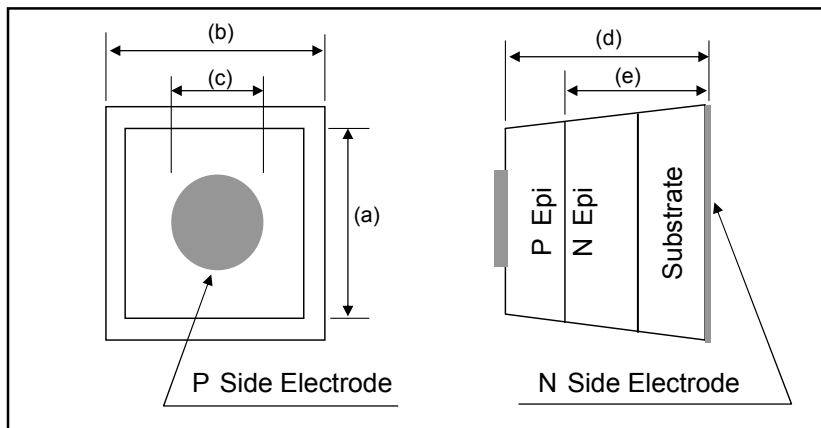
**3. Electro-Optical Characteristics**

| Parameter       | Symbol          | Min | Typ  | Max  | Unit | Condition |         |
|-----------------|-----------------|-----|------|------|------|-----------|---------|
| Forward Voltage | $V_F$           |     | 1.3  | 1.45 | V    | IF=20mA   |         |
| Reverse Voltage | $V_R$           | 8   |      |      | V    | IR=10uA   |         |
| Power           | Po              | A   | 1.05 |      | 1.13 | mW        | IF=20mA |
|                 |                 | B   | 1.13 |      | 1.21 |           |         |
|                 |                 | C   | 1.21 |      | 1.28 |           |         |
|                 |                 | D   | 1.28 |      | 1.36 |           |         |
|                 |                 | E   | 1.36 |      | 1.44 |           |         |
|                 |                 | F   | 1.44 |      | 1.52 |           |         |
|                 |                 | G   | 1.52 |      | 1.59 |           |         |
|                 |                 | G1  | 1.59 |      | 1.69 |           |         |
| Wavelength      | $\lambda_P$     |     | 940  |      | nm   | IF=20mA   |         |
|                 | $\Delta\lambda$ |     | 45   |      | nm   | IF=20mA   |         |

※ Note : Power is measured by Sorter E/T system with bare chip.

**4. Mechanical Data**

- (a) Emission Area ----- 7mil x 7mil
- (b) Bottom Area ----- 8mil x 8mil
- (c) Bonding Pad ----- 100um
- (d) Chip Thickness ----- 9.0mil (8mil Available)
- (e) Junction Height ----- 4.7mil



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